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ON Semiconductor®

Energy Efficient Innovations

Product Overview

MJD210: 5.0 A, 25 V PNP Bipolar Power Transistor

For complete documentation, see the data sheet.

The Bipolar Power Transistor is designed for low voltage, low power, high gain audio amplifier applications. The MJD200 (NPN) and MJD210 (PNP) are complementary devices.

Features

- Collector-Emitter Sustaining Voltage - $V_{CEO(sus)}$ = 25 Vdc (Min) @ I_C = 10 mAdc
- High DC Current Gain - h_{FE} = 70 (Min) @ I_C = 500 mAdc
  = 45 (Min) @ I_C = 2 Adc
  = 10 (Min) @ I_C = 5 Adc
- Low Collector-Emitter Saturation Voltage - $V_{CE(sat)}$
  = 0.30 Vdc (Max) @ I_C = 500 mAdc
  = 0.75 Vdc (Max) @ I_C = 2.0 Adc
- High Current-Gain - Bandwidth Product - f_T = 65 MHz (Min) @ I_C = 100 mAdc
- Annular Construction for Low Leakage - I_{CBO} = 100 nAdc @ Rated V_{CB}
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant
- MJD200 is the complementary NPN device

Part Electrical Specifications

Product	Compliance	Status	Polarity	Type	$V_{CE(sat)}$ Max (V)	I_C Cont. (A)	V_{CEO} Min (V)	V_{CBO} (V)	V_{EBO} (V)	$V_{BE(sat)}$ (V)	$V_{BE(on)}$ (V)	h_{FE} Min	h_{FE} Max	f_T Min (MHz)	P_{TM} Max (W)	Package Type
MJD210G	Pb-free Halide free	Active	PNP	General Purpose	1.8	5	25	40	8	2.5	1.6	45	180	3	12.5	DPAK-3
MJD210RLG	Pb-free Halide free	Active	PNP	General Purpose	1.8	5	25	40	8	2.5	1.6	45	180	3	12.5	DPAK-3
MJD210T4G	Pb-free Halide free	Active	PNP	General Purpose	1.8	5	25	40	8	2.5	1.6	45	180	3	12.5	DPAK-3
MJD210TF	Pb-free Halide free	Active	PNP	General Purpose	1.8	5	25	40	8	2.5	1.6	45	180	3	12.5	DPAK-3
NJVMJD210T4G	AEC Qualified PPAP Capable Pb-free Halide free	Active	PNP	General Purpose	1.8	5	25	40	8	2.5	1.6	45	180	3	12.5	DPAK-3

For more information please contact your local sales support at www.onsemi.com.

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